

# RJK2006DPJ, RJK2006DPE, RJK2006DPF

Silicon N Channel MOS FET  
High Speed Power Switching

REJ03G0512-0200

Rev.2.00

Nov 19, 2009

## Features

- Low on-resistance
- Low leakage current
- High speed switching

## Outline

RENESAS Package code: PRSS0004AE-A (Package name: LDKPAK(L))	: PRSS0004AE-B LDKPAK(S)-(1)	: PRSS0004AE-C LDKPAK(S)-(2)	<p>1. Gate 2. Drain 3. Source 4. Drain</p>
<p>RJK2006DPJ</p>	<p>RJK2006DPE</p>	<p>RJK2006DPF</p>	

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to Source voltage	$V_{DSS}$	200	V
Gate to Source voltage	$V_{GSS}$	±30	V
Drain current	$I_D$	40	A
Drain peak current	$I_{D(pulse)}$ <sup>Note1</sup>	100	A
Body-Drain diode reverse Drain current	$I_{DR}$	40	A
Body-Drain diode reverse Drain peak current	$I_{DR(pulse)}$ <sup>Note1</sup>	100	A
Avalanche current	$I_{AP}$ <sup>Note3</sup>	27	A
Avalanche energy	$E_{AR}$ <sup>Note3</sup>	48.6	mJ
Channel dissipation	$P_{ch}$ <sup>Note2</sup>	100	W
Channel to case thermal impedance	$\theta_{ch-c}$	1.25	°C/W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

Notes: 1.  $PW \leq 10 \mu s$ , duty cycle  $\leq 1\%$

2. Value at  $T_c = 25^\circ C$

3.  $STch = 25^\circ C$ ,  $T_{ch} \leq 150^\circ C$

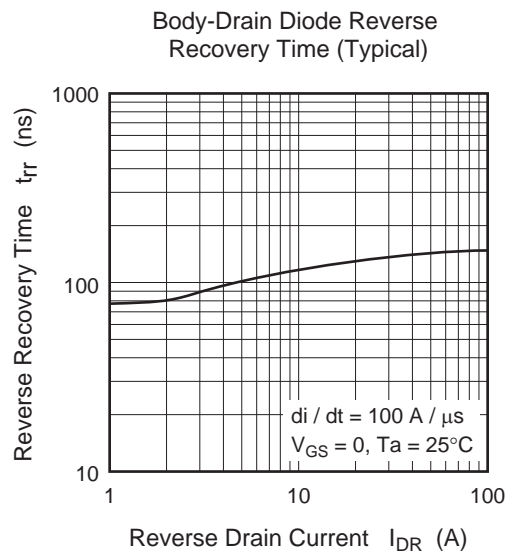
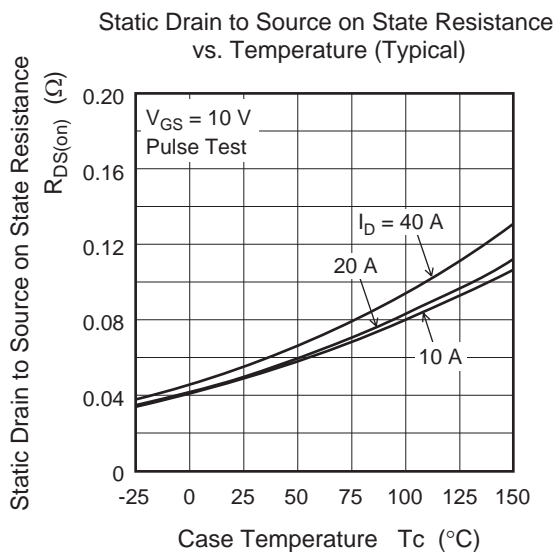
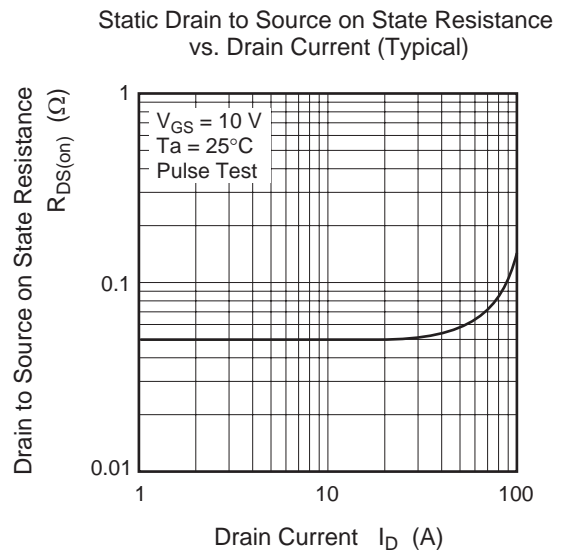
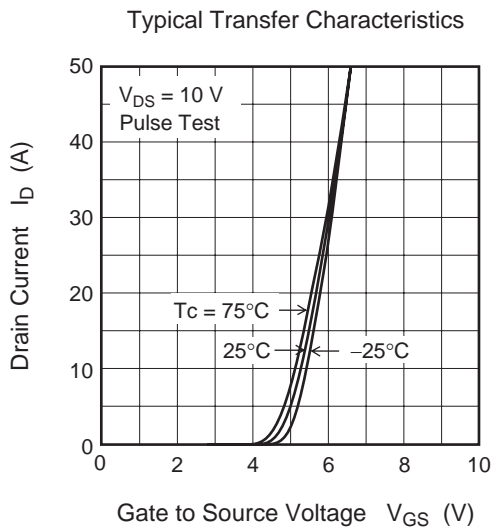
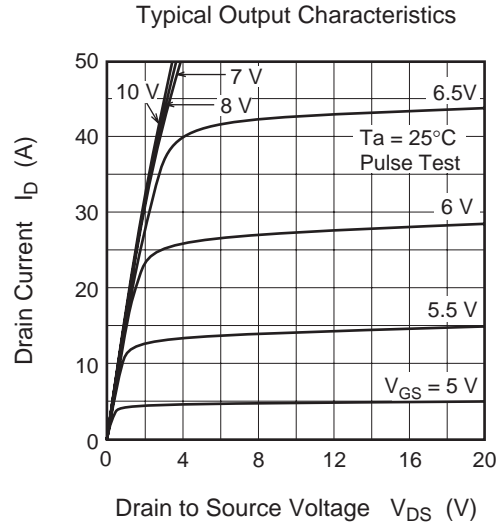
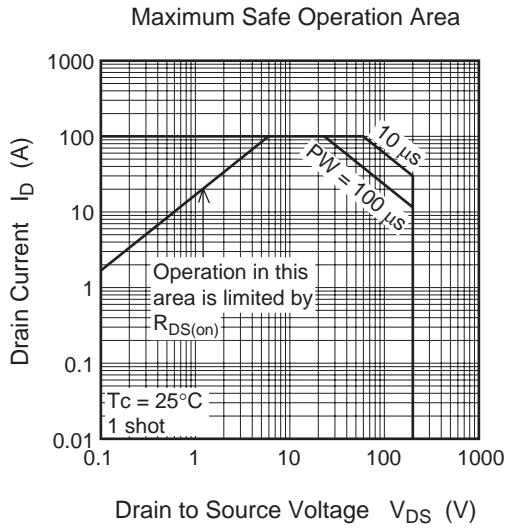
## Electrical Characteristics

(Ta = 25°C)

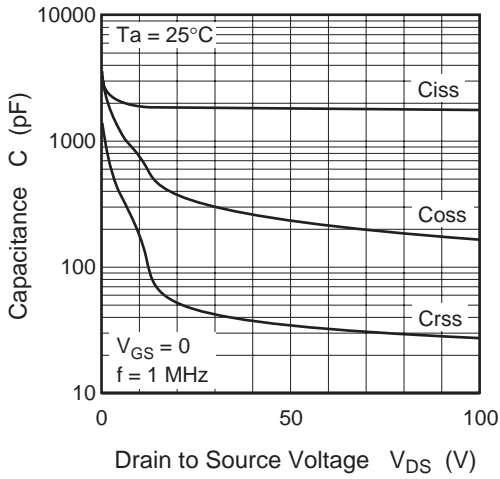
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to Source breakdown voltage	$V_{(BR)DSS}$	200	—	—	V	$I_D = 10 \text{ mA}$ , $V_{GS} = 0$
Zero Gate voltage drain current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 200 \text{ V}$ , $V_{GS} = 0$
Gate to Source leak current	$I_{GSS}$	—	—	$\pm 0.1$	$\mu\text{A}$	$V_{GS} = \pm 30 \text{ V}$ , $V_{DS} = 0$
Gate to Source cutoff voltage	$V_{GS(off)}$	3.0	—	4.5	V	$V_{DS} = 10 \text{ V}$ , $I_D = 1 \text{ mA}$
Forward transfer admittance	$ y_{fs} $	15	26	—	S	$I_D = 20 \text{ A}$ , $V_{DS} = 10 \text{ V}$ <sup>Note4</sup>
Static Drain to Source on state resistance	$R_{DS(on)}$	—	0.052	0.059	$\Omega$	$I_D = 20 \text{ A}$ , $V_{GS} = 10 \text{ V}$ <sup>Note4</sup>
Input capacitance	$C_{iss}$	—	1800	—	pF	$V_{DS} = 25 \text{ V}$
Output capacitance	$C_{oss}$	—	330	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	43	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	30	—	ns	$I_D = 20 \text{ A}$
Rise time	$t_r$	—	180	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	85	—	ns	$R_L = 5 \Omega$
Fall time	$t_f$	—	100	—	ns	$R_g = 10 \Omega$
Total Gate charge	$Q_g$	—	43	—	nC	$V_{DD} = 160 \text{ V}$
Gate to Source charge	$Q_{gs}$	—	11	—	nC	$V_{GS} = 10 \text{ V}$
Gate to Drain charge	$Q_{gd}$	—	20	—	nC	$I_D = 40 \text{ A}$
Body-Drain diode forward voltage	$V_{DF}$	—	1.0	1.5	V	$I_F = 40 \text{ A}$ , $V_{GS} = 0$ <sup>Note4</sup>
Body-Drain diode reverse recovery time	$t_{rr}$	—	150	—	ns	$I_F = 40 \text{ A}$ , $V_{GS} = 0$
Body-Drain diode reverse recovery charge	$Q_{rr}$	—	0.8	—	$\mu\text{C}$	$di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

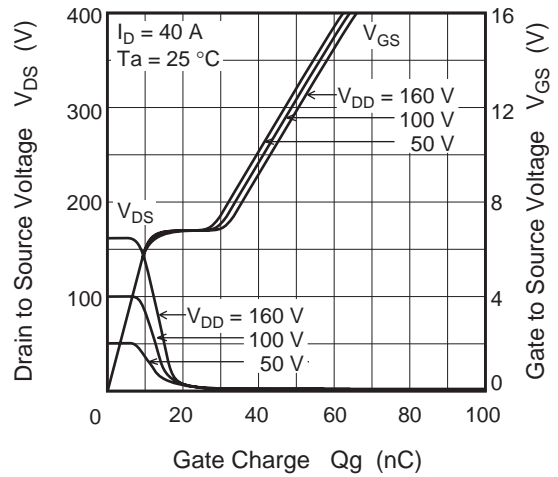
### Main Characteristics



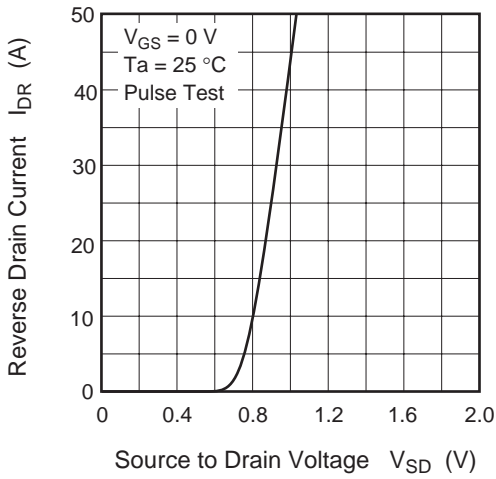
Typical Capacitance vs. Drain to Source Voltage



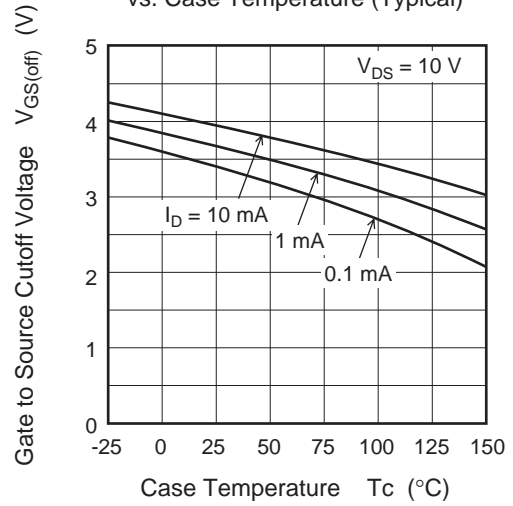
Dynamic Input Characteristics (Typical)

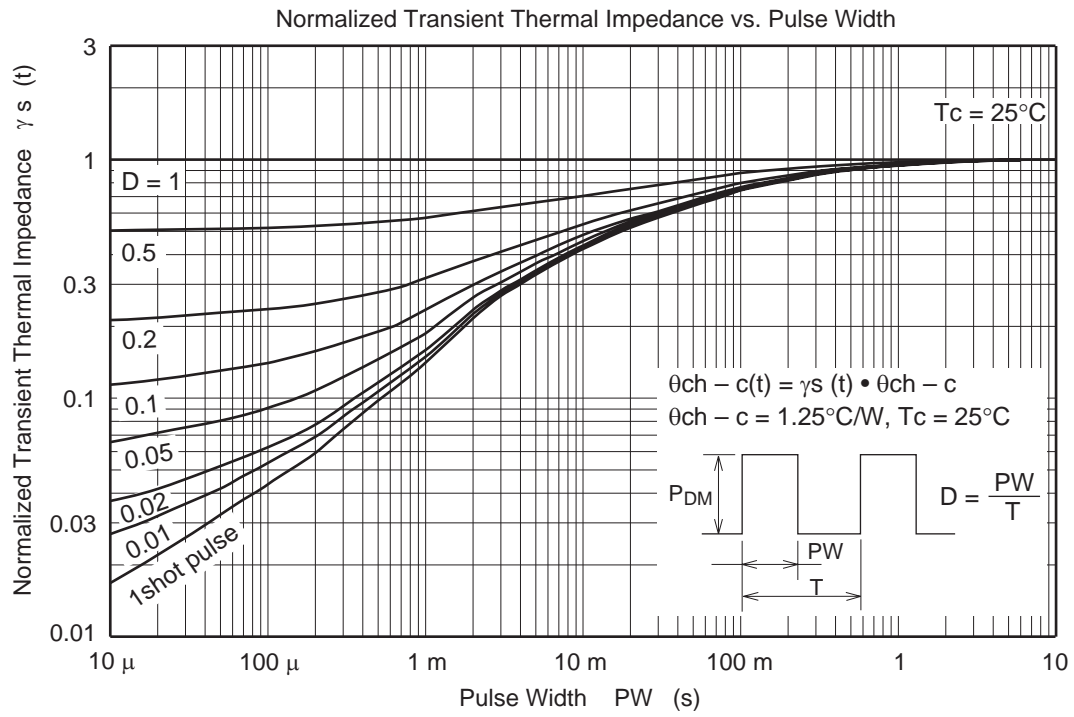


Reverse Drain Current vs. Source to Drain Voltage (Typical)

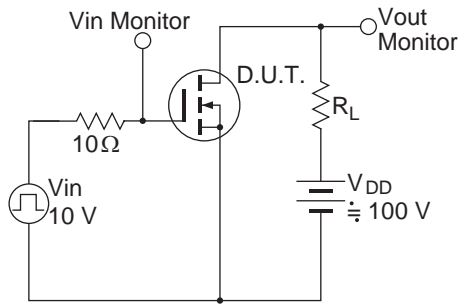


Gate to Source Cutoff Voltage vs. Case Temperature (Typical)

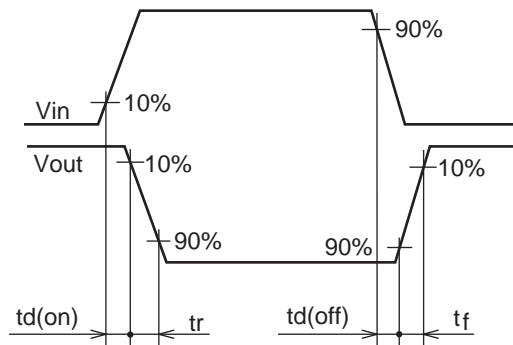




Switching Time Test Circuit

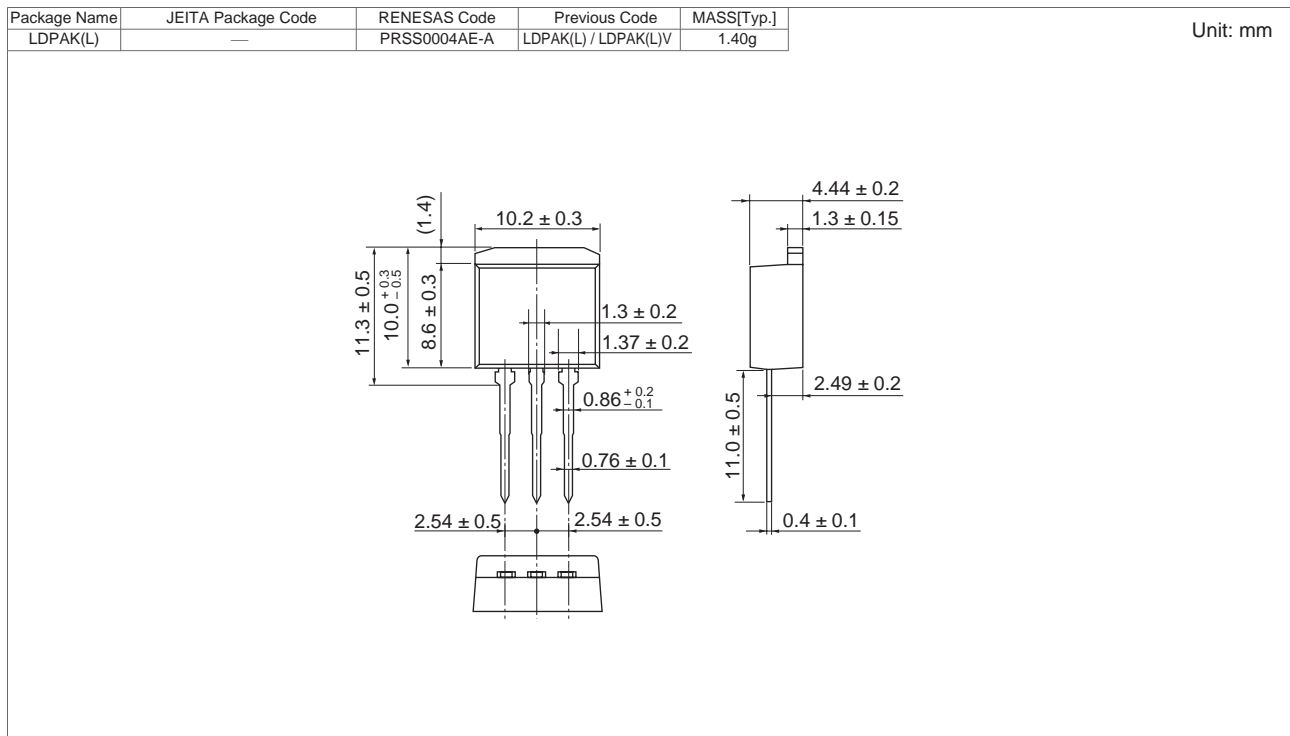


Waveform

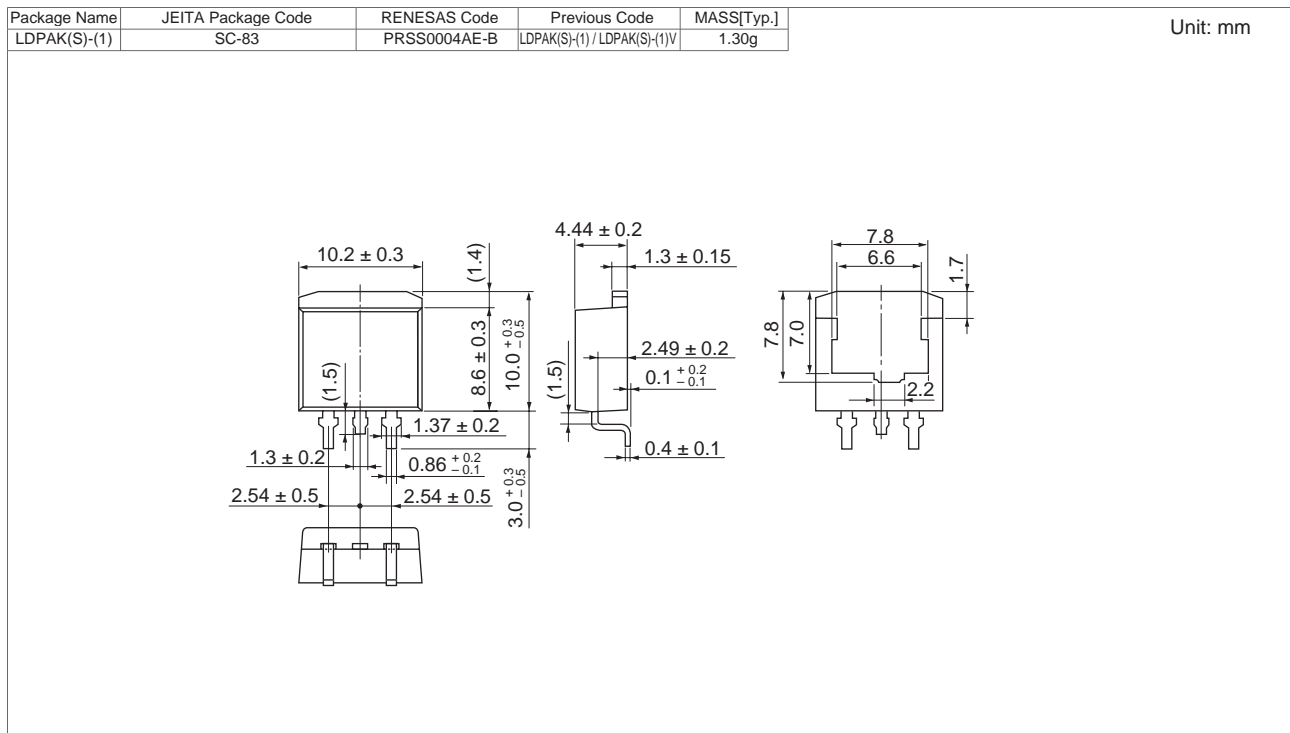


## Package Dimensions

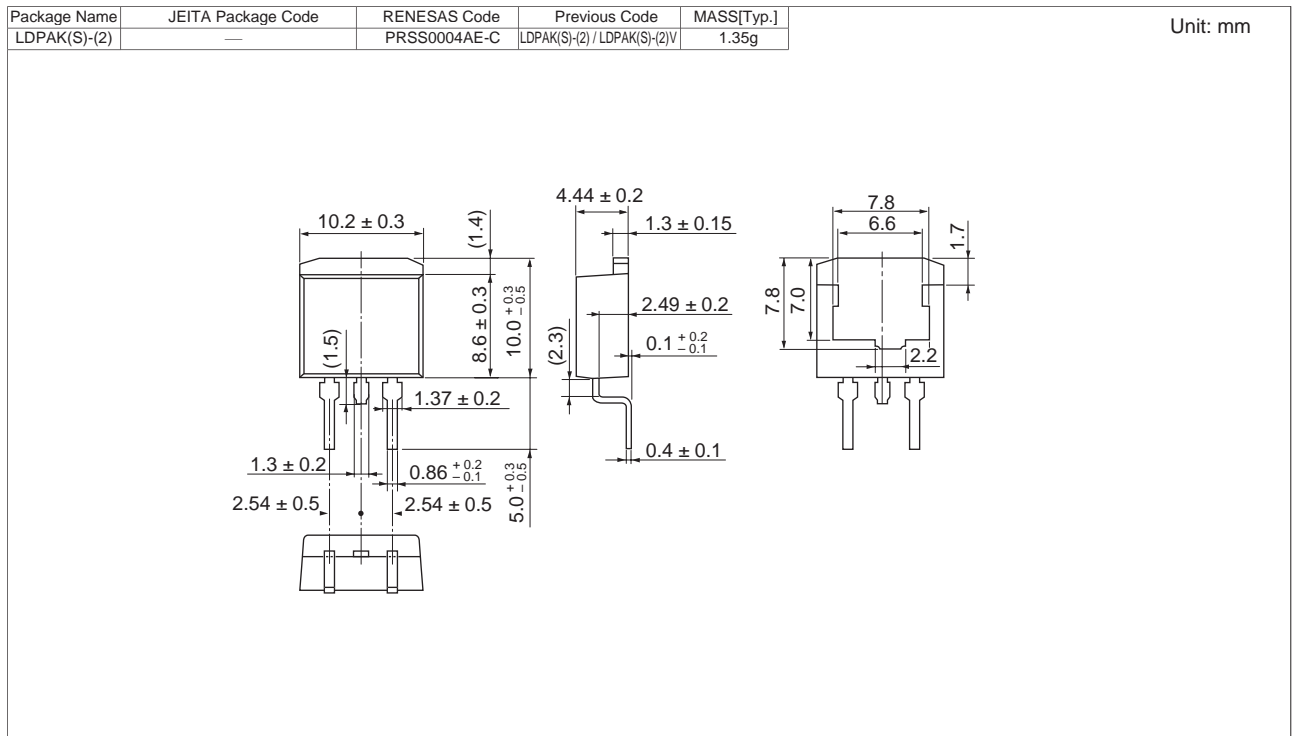
### • RJK2006DPJ



### • RJK2006DPE



• RJK2006DPF



Ordering Information

Part No.	Quantity	Shipping Container
RJK2006DPE-00-J3	1000 pcs	Taping

Notes:

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